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NTE460 Silicon P-Channel JFET Transistor AF Amp TO72 Type Package

Absolute Maximum Ratings:

Drain-Gate Voltage, V_{DG}	20V
Reverse Gate-Source Voltage, V_{GSR}	20V
Gate Current, I_G	10mA
Total Device Dissipation ($T_A = +25^\circ C$), P_D	0.3W
Derate above $25^\circ C$	1.7mW/ $^\circ C$
Storage Temperature Range, T_{stg}	-65° to $+200^\circ C$

Electrical Characteristics: ($T_A = +25^\circ C$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
OFF Characteristics						
Gate-Source Breakdown Voltage	$V_{(BR)GSS}$	$I_G = 10^\circ A, V_{DS} = 0$	20	-	-	V
Gate Reverse Current	I_{GSS}	$V_{GS} = 10V, V_{DS} = 0$	-	-	10	nA
		$V_{GS} = 10V, V_{DS} = 0, T_A = +150^\circ C$	-	-	10	$^\circ A$
ON Characteristics						
Zero-Gate-Voltage Drain Current	I_{DSS}	$V_{DS} = -10V, V_{GS} = 0$, Note 1	2.0	-	6.0	mA
Gate-Source Voltage	V_{GS}	$V_{DG} = -15V, I_D = 10^\circ A$	-	-	6.0	V
Drain-Source Resistance	r_{DS}	$I_D = 100^\circ A, V_{GS} = 0$	-	-	800	\leq
Small-Signal Characteristics						
Forward Transfer Admittance	$ y_{fs} $	$V_{DS} = 10V, I_D = 2mA, f = 1kHz$, Note 1	1500	-	3000	$^\circ$ mhos
		$V_{DS} = 10V, I_D = 2mA, f = 10MHz$, Note 1	1350	-	-	$^\circ$ mhos
Output Admittance	$ y_{os} $	$V_{DS} = 10V, I_D = 2mA, f = 1kHz$	-	-	40	$^\circ$ mhos
Reverse Transfer Conductance	$ y_{rs} $	$V_{DS} = 10V, I_D = 2mA, f = 1kHz$	-	-	0.1	$^\circ$ mhos
Input Conductance	$ y_{is} $	$V_{DS} = 10V, I_D = 2mA, f = 1kHz$	-	-	0.2	$^\circ$ mhos
Input Capacitance	C_{iss}	$V_{DS} = 10V, V_{GS} = 1V, f = 1MHz$	-	-	20	pF
Functional Characteristics						
Noise Figure	NF	$V_{DS} = -5V, I_D = 1mA, R_g = 1M\leq, f = 1kHz$	-	-	3.0	dB

Note 1. Pulse Test: PulseWidth \leq 630ms, Duty Cycle \leq 10%.

